# **General Purpose Transistors**

# **PNP Silicon**

### **Features**

• Pb-Free Packages are Available\*

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	40	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current - Continuous	Ic	200	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Power Dissipation @ T <sub>A</sub> = 60°C	P <sub>D</sub>	250	mW
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

# THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

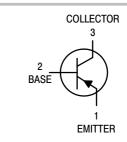
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

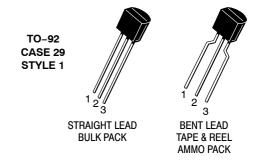
1. Indicates Data in addition to JEDEC Requirements.



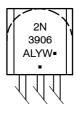
# ON Semiconductor®

http://onsemi.com





#### **MARKING DIAGRAM**



A = Assembly Location

= Wafer Lot

Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

1

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

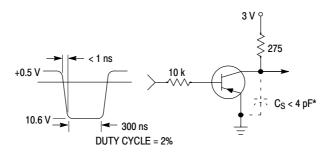
Characteristic				Min	Max	Unit
OFF CHARACTERIS	TICS				•	
Collector – Emitter Breakdown Voltage (Note 2) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)		V <sub>(BR)CEO</sub>	40	-	Vdc	
Collector - Base Brea	Collector – Base Breakdown Voltage $(I_C = 10 \mu Adc, I_E = 0)$		V <sub>(BR)CBO</sub>	40	-	Vdc
Emitter - Base Break	down Voltage	$(I_E = 10 \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	_	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub>		(V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	-	50	nAdc
Collector Cutoff Curre	ent	(V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERIST	TICS (Note 2)			•		-
(l <sub>c</sub> (l (l (l		$ \begin{array}{l} (I_{C}=0.1 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=50 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=100 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \end{array} $	h <sub>FE</sub>	60 80 100 60 30	- 300 - -	_
Collector – Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$			V <sub>CE(sat)</sub>	- -	0.25 0.4	Vdc
Base – Emitter Saturation Voltage $ \begin{aligned} &\text{(I}_{C} = 10 \text{ mAdc, I}_{B} = 1.0 \text{ mAdc)} \\ &\text{(I}_{C} = 50 \text{ mAdc, I}_{B} = 5.0 \text{ mAdc)} \end{aligned} $		V <sub>BE(sat)</sub>	0.65 -	0.85 0.95	Vdc	
SMALL-SIGNAL CH	IARACTERISTICS					
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)		f <sub>T</sub>	250	-	MHz	
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		(V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	4.5	pF
Input Capacitance		(V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	10	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>ie</sub>	2.0	12	kΩ	
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>re</sub>	0.1	10	X 10 <sup>-4</sup>	
Small–Signal Current Gain ( $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$ )		h <sub>fe</sub>	100	400	-	
Output Admittance ( $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$ )		h <sub>oe</sub>	3.0	60	μmhos	
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz)		NF	-	4.0	dB	
SWITCHING CHARA	CTERISTICS					
Delay Time	Delay Time $(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = 0.5 \text{ Vdc},$		t <sub>d</sub>	-	35	ns
Rise Time		10 mAdc, I <sub>B1</sub> = 1.0 mAdc)		-	35	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 1	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$		-	225	ns
Fall Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)		t <sub>f</sub>	-	75	ns

<sup>2.</sup> Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

# **ORDERING INFORMATION**

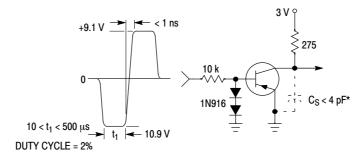
Device	Package	Shipping <sup>†</sup>
2N3906	TO-92	5000 Units / Bulk
2N3906G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3906RL1	TO-92	2000 / Tape & Reel
2N3906RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3906RLRA	TO-92	2000 / Tape & Reel
2N3906RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3906RLRM	TO-92	2000 / Tape & Ammo Box
2N3906RLRMG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
2N3906RLRP	TO-92	2000 / Tape & Ammo Box
2N3906RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



<sup>\*</sup> Total shunt capacitance of test jig and connectors

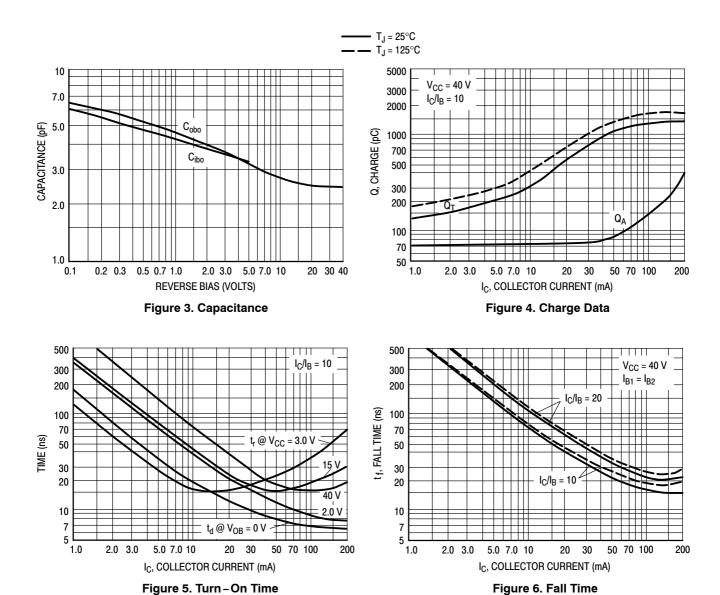
Figure 1. Delay and Rise Time Equivalent Test Circuit



<sup>\*</sup> Total shunt capacitance of test jig and connectors

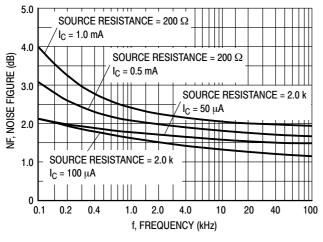
Figure 2. Storage and Fall Time Equivalent Test Circuit

# **TYPICAL TRANSIENT CHARACTERISTICS**



# TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS **NOISE FIGURE VARIATIONS**

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$ 



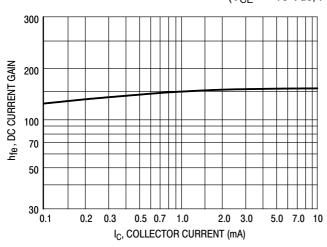
12 f = 1.0 kHz10 NF, NOISE FIGURE (dB)  $I_C$  = 50  $\mu$ A  $I_C = 100 \mu A$ 0.2 2.0 4.0 0.4 1.0 10 20 40 0.1 100 R<sub>q</sub>, SOURCE RESISTANCE (k OHMS)

Figure 7.

Figure 8.

# **h PARAMETERS**

( $V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C}$ )



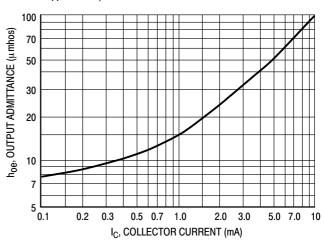
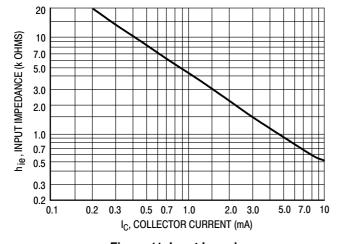


Figure 9. Current Gain

Figure 10. Output Admittance



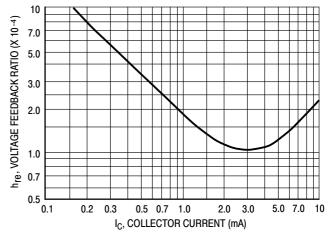


Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

### TYPICAL STATIC CHARACTERISTICS

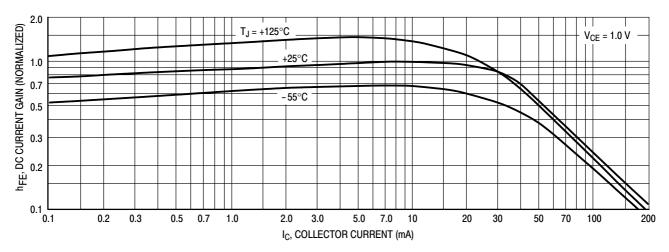


Figure 13. DC Current Gain

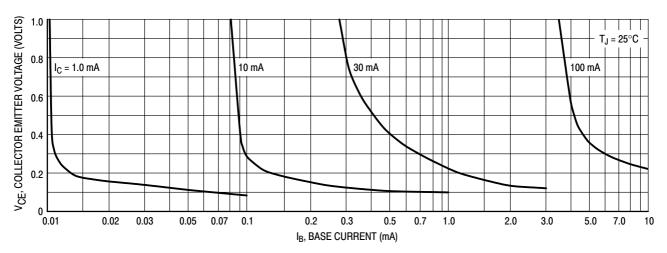


Figure 14. Collector Saturation Region

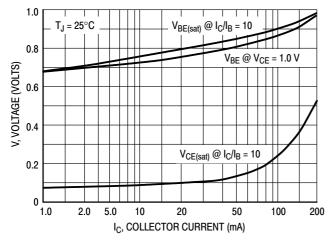


Figure 15. "ON" Voltages

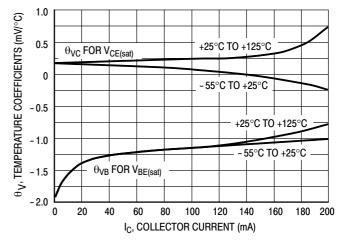
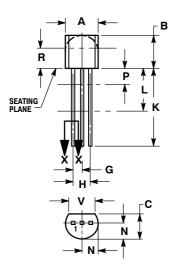


Figure 16. Temperature Coefficients

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM** 



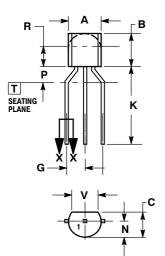
STRAIGHT LEAD **BULK PACK** 



## NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD** TAPE & REEL AMMO PACK



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND
  DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

STYLE 1:

PIN 1 FMITTER

BASE

COLLECTOR

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